MC74LCX125

Low-Voltage CMOS Quad Buffer

With 5 V−Tolerant Inputs and Outputs (3−State, Non−Inverting)

The MC74LCX125 is a high performance, non−inverting quad buffer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX125 inputs to be safely driven from 5.0 V devices. The MC74LCX125 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable ($\overline{OE}n$) inputs, when HIGH, disable the outputs by placing them in a HIGH Z condition.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant − Interface Capability With 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0$ V
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in all Three Logic States (10 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V
  Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
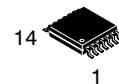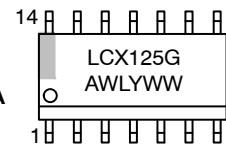- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant
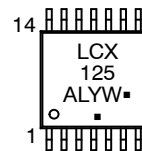
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MARKING DIAGRAMS
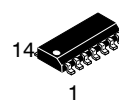
SOIC−14
D SUFFIX
CASE 751A

```
LCX125G
AWLYWW
```

TSSOP−14
DT SUFFIX
CASE 948G

```
LCX
125
ALYW■
```

A	=	Assembly Location
L, WL	=	Wafer Lot
Y, YY	=	Year
W, WW	=	Work Week
G or ■	=	Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.
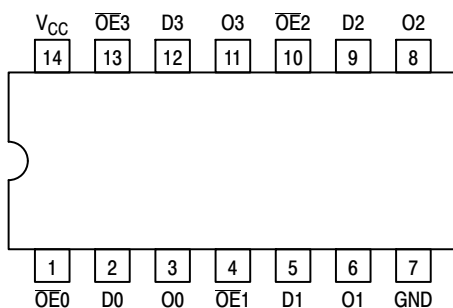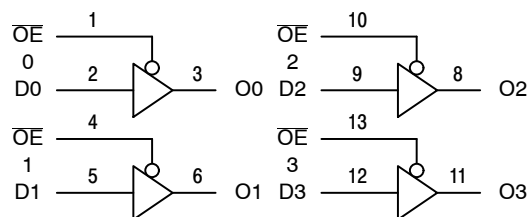
1

MC74LCX125

Figure 1. Pinout: 14−Lead (Top View)

Figure 2. Logic Diagram

PIN NAMES

Pins	Function
$\overline{OE}n$	Output Enable Inputs
Dn	Data Inputs
On	3−State Outputs

TRUTH TABLE

INPUTS		OUTPUTS
$\overline{OE}n$	Dn	On
L	L	L
L	H	H
H	X	Z

H = High Voltage Level
L = Low Voltage Level
Z = High Impedance State
X = High or Low Voltage Level and Transitions Are
Acceptable; for I_{CC} reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V_{CC}	DC Supply Voltage	−0.5 to +7.0		V
V_I	DC Input Voltage	$-0.5 \le V_I \le +7.0$		V
V_O	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3−State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State. (Note 1)	V
I_{IK}	DC Input Diode Current	−50	$V_I <$ GND	mA
I_{OK}	DC Output Diode Current	−50	$V_O <$ GND	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current Per Supply Pin	±100		mA
I_{GND}	DC Ground Current Per Ground Pin	±100		mA
T_{STG}	Storage Temperature Range	−65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units

V_{CC}	Supply Voltage
	  Operating
	  Data Retention Only
		
		2.0
		1.5
			
			2.5, 3.3
			2.5, 3.3
				
				3.6
				3.6
					V

V_I	Input Voltage	0		5.5	V

V_O	Output Voltage
	  HIGH or LOW State
	  3−State
		
		0
		0
				
				V_{CC}
				5.5
					V

I_{OH}	HIGH Level Output Current
	  V_{CC} = 3.0 V − 3.6 V
	  V_{CC} = 2.7 V − 3.0 V
	  V_{CC} = 2.3 V − 2.7 V
				
				−24
				−12
				−8
					mA

I_{OL}	LOW Level Output Current
	  V_{CC} = 3.0 V − 3.6 V
	  V_{CC} = 2.7 V − 3.0 V
	  V_{CC} = 2.3 V − 2.7 V
				
				+24
				+12
				+8
					mA

T_A	Operating Free−Air Temperature	−40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = −40°C to +85°C Min	T_A = −40°C to +85°C Max	Units
V_{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V_{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V_{CC} ≤ 3.6 V	2.0		
V_{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V_{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V_{CC} ≤ 3.6 V		0.8	
V_{OH}	HIGH Level Output Voltage	2.3 V ≤ V_{CC} ≤ 3.6 V; I_{OL} = 100 μA	V_{CC} − 0.2		V
		V_{CC} = 2.3 V; I_{OH} = −8 mA	1.8		
		V_{CC} = 2.7 V; I_{OH} = −12 mA	2.2		
		V_{CC} = 3.0 V; I_{OH} = −18 mA	2.4		
		V_{CC} = 3.0 V; I_{OH} = −24 mA	2.2		
V_{OL}	LOW Level Output Voltage	2.3 V ≤ V_{CC} ≤ 3.6 V; I_{OL} = 100 μA		0.2	V
		V_{CC} = 2.3 V; I_{OL} = 8 mA		0.6	
		V_{CC} = 2.7 V; I_{OL} = 12 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 16 mA		0.4	
		V_{CC} = 3.0 V; I_{OL} = 24 mA		0.55	
I_{OZ}	3−State Output Current	V_{CC} = 3.6 V, V_{IN} = V_{IH} or V_{IL}, V_{OUT} = 0 to 5.5 V		±5	μA
I_{OFF}	Power Off Leakage Current	V_{CC} = 0, V_{IN} = 5.5 V or V_{OUT} = 5.5 V		10	μA
I_{IN}	Input Leakage Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		±5	μA
I_{CC}	Quiescent Supply Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		10	μA
ΔI_{CC}	Increase in I_{CC} per Input	2.3 ≤ V_{CC} ≤ 3.6 V; V_{IH} = V_{CC} − 0.6 V		500	μA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS ($t_R = t_F = 2.5$ ns; $R_L = 500\ \Omega$)

Symbol	Parameter	Waveform	Limits						Units
			$T_A = -40°C$ to $+85°C$						
			$V_{CC} = 3.3$ V $\pm$ 0.3 V		$V_{CC} = 2.7$ V		$V_{CC} = 2.5$ V $\pm$ 0.2 V		
			$C_L = 50$ pF		$C_L = 50$ pF		$C_L = 30$ pF		
			Min	Max	Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Time Input to Output	1	1.5 1.5	6.0 6.0	1.5 1.5	6.5 6.5	1.5 1.5	7.2 7.2	ns
t_{PZH} t_{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	9.1 9.1	ns
t_{PHZ} t_{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	6.0 6.0	1.5 1.5	7.0 7.0	1.5 1.5	7.2 7.2	ns
t_{OSHL} t_{OSLH}	Output−to−Output Skew (Note 3)			1.0 1.0					ns

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH−to−LOW (t_{OSHL}) or LOW−to−HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	$T_A = +25°C$			Units
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3$ V, $C_L = 50$ pF, $V_{IH} = 3.3$ V, $V_{IL} = 0$ V $V_{CC} = 2.5$ V, $C_L = 30$ pF, $V_{IH} = 2.5$ V, $V_{IL} = 0$ V		0.8 0.6		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3$ V, $C_L = 50$ pF, $V_{IH} = 3.3$ V, $V_{IL} = 0$ V $V_{CC} = 2.5$ V, $C_L = 30$ pF, $V_{IH} = 2.5$ V, $V_{IL} = 0$ V		−0.8 −0.6		V

4. Number of outputs defined as "n". Measured with "n−1" outputs switching from HIGH−to−LOW or LOW−to−HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} = 3.3$ V, $V_I = 0$ V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	$V_{CC} = 3.3$ V, $V_I = 0$ V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	10 MHz, $V_{CC} = 3.3$ V, $V_I = 0$ V or V_{CC}	25	pF

ORDERING INFORMATION

Device	Package	Shipping[†]
MC74LCX125DG	SOIC−14 (Pb−Free)	55 Units / Rail
MC74LCX125DR2G	SOIC−14 (Pb−Free)	2500 Tape & Reel
MC74LCX125DTG	TSSOP−14 (Pb−Free)	96 Units / Rail
MC74LCX125DTR2G	TSSOP−14 (Pb−Free)	2500 Tape & Reel
NLVLCX125DTR2G	TSSOP−14* (Pb−Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
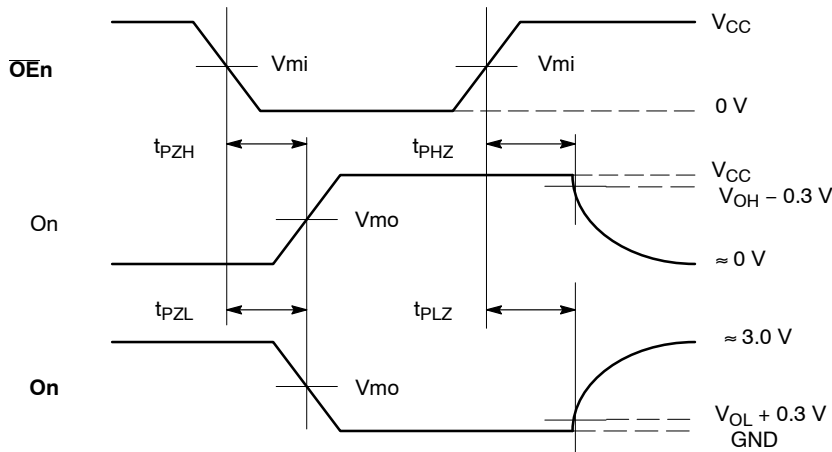*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified.

MC74LCX125
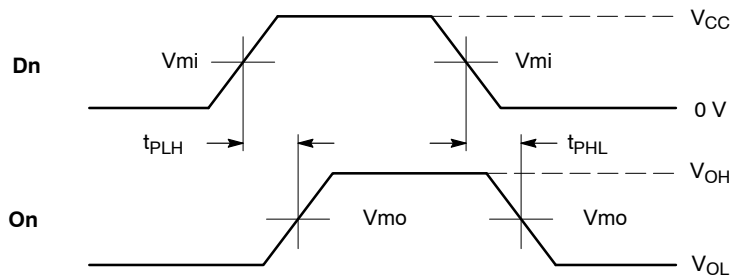
WAVEFORM 1 – PROPAGATION DELAYS
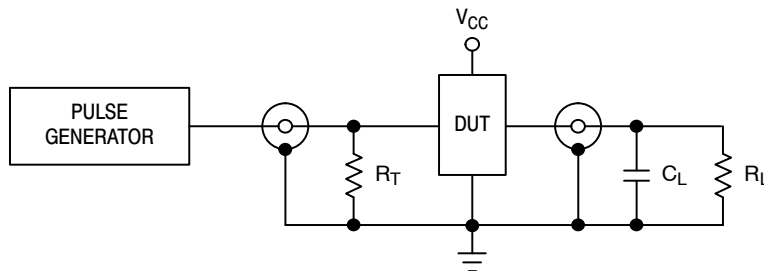$t_R = t_F = 2.5$ ns, 10% to 90%; $f = 1$ MHz; $t_W = 500$ ns

WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES
$t_R = t_F = 2.5$ ns, 10% to 90%; $f = 1$ MHz; $t_W = 500$ ns

Symbol	V_{CC}		
	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V
Vmi	1.5 V	1.5 V	$V_{CC}/2$
Vmo	1.5 V	1.5 V	$V_{CC}/2$

Figure 3. AC Waveforms

$C_L = $ 50 pF at $V_{CC} = $ 3.3 ±0.3 V or equivalent (includes jig and probe capacitance)
$C_L = $ 30 pF at $V_{CC} = $ 2.5 ±0.2 V or equivalent (includes jig and probe capacitance)
$R_L = R_1 = 500 \ \Omega$ or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

http://onsemi.com

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

14

1

SCALE 1:1
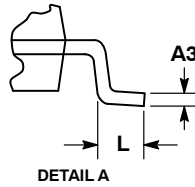
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DETAIL A

DETAIL A

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

SEATING PLANE

SOLDERING FOOTPRINT*

6.50

14X 1.18

1

1.27 PITCH

14X 0.58

DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

14

XXXXXXXXXG
AWLYWW

1

XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.
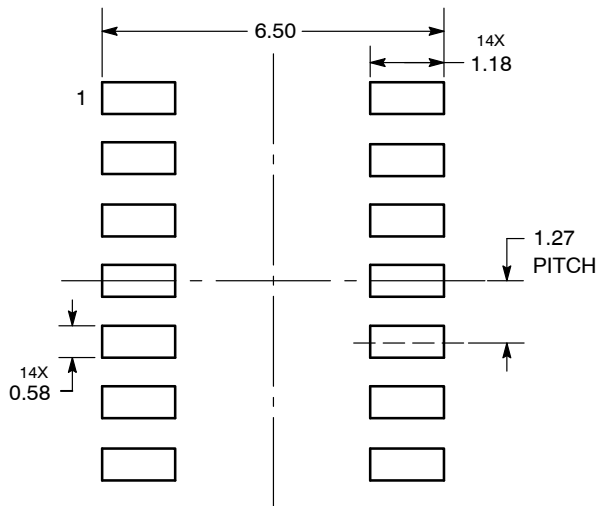
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−14 NB		PAGE 1 OF 2

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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DESCRIPTION:	SOIC−14 NB		PAGE 2 OF 2

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TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016

14

SCALE 2:1

1

14X **K** REF

$\oplus$ | 0.10 (0.004) Ⓜ | T | U Ⓢ | V Ⓢ

$\triangle$ | 0.15 (0.006) | T | U Ⓢ

2X **L**/2

L

PIN 1 IDENT.

14   8

B
−U−

1   7

A
−V−

$\triangle$ | 0.15 (0.006) | T | U Ⓢ

N

0.25 (0.010)

M

N

F

DETAIL E

K

K1

J J1

SECTION N−N

C

$\triangle$ | 0.10 (0.004)

−T− SEATING PLANE

D   G   H

−W−

DETAIL E

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*

14

XXXX
XXXX
ALYW∎

1

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
∎ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "∎", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT

7.06

1

0.65
PITCH

14X
0.36

14X
1.26

DIMENSIONS: MILLIMETERS

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DESCRIPTION:	**TSSOP−14 WB**		**PAGE 1 OF 1**

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